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UNDER ACT XIII OF 1989)
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DECLARATION

I, **KHOIROM KABITA** bearing Ph.D. Registration No Ph.D./2037/12 dated 12/09/12, & UNIVERSITY REGISTRATION NO: 24-110033327 of 2011-2012 hereby declare that the subject matter of the thesis entitled “**DFT STUDY OF SOME SELECTED BINARY COMPOUND SEMICONDUCTORS: ELECTRONIC STRUCTURES AND ELASTIC PROPERTIES**” is the record of work done by me and that the contents of this thesis did not form the basis for award of any award to me or to anybody else to the best of my knowledge. The thesis has not been submitted in any other University/Institute.

This thesis is being submitted to Assam University for the degree of Doctor of Philosophy in Physics.

Place:

Date:

(Khoirom Kabita)

ACKNOWLEDGEMENT

I take this opportunity to express my deep sense of gratitude and thanks to my mentor and guide, Dr. B Indrajit Sharma, Associate Professor, Department of Physics, Assam University Silchar, whose dedication, keen interest and overwhelming attitude to help his students has been solely and mainly responsible in completion of my thesis work. His timely advice, meticulous scrutiny, scholarly advice and scientific approach has helped me to a very great extent to accomplish my work. I could not have imagined having a better advisor and mentor for my Ph.D study.

I would like to also show my gratitude all the Faculty members, Lab Staffs and Office Staffs of the Department of Physics, for their insightful comments and encouragement which incited me to widen my research from various perspectives.

I also thank my past and present research fellow mates of the Department of Physics and other Departments for sharing their pearls of wisdom with me during the course of my research.

I would like to thank Dean, School of Physical Science for all official logistic support and Assam University Silchar, for providing me with University fellowship as it would have been very difficult to complete my Ph.D work without this financial support.

Lastly but not the least I would like to thank my family: my grandmother, my parents and brothers for supporting me spiritually throughout my Ph.D and my life in general and also pray to God for the time to come.

(Khoirom Kabita)

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